

 I_D

PHD101NQ03LT

N-channel TrenchMOS logic level FET Rev. 5 — 31 October 2011

Product data sheet

Product profile 1.

1.1 General description

Logic level N-channel enhancement mode Field-Effect Transistor (FET) in a plastic package using TrenchMOS technology. This product is designed and qualified for use in computing, communications, consumer and industrial applications only.

1.2 Features and benefits

- Low conduction losses due to low on-state resistance
- Simple gate drive required due to low gate charge

1.3 Applications

DC-to-DC converters

1.4 Quick reference data

Table 1. **Quick reference data** Symbol Parameter Conditions Min Тур Max Unit drain-source voltage T_i ≥ 25 °C; T_i ≤ 175 °C 30 ۷ VDS - $T_{mb} = 25 \text{ °C}; V_{GS} = 10 \text{ V}; \text{ see Figure 1};$ drain current _ 75 А _ see Figure 3 P_{tot} total power dissipation T_{mb} = 25 °C; see Figure 2 166 W --Static characteristics drain-source on-state $V_{GS} = 10 \text{ V}; I_D = 25 \text{ A}; T_i = 25 \text{ °C};$ 4.5 5.5 mΩ **R**_{DSon} _ resistance see Figure 9; see Figure 10 **Dynamic characteristics** nC Q_{GD} gate-drain charge $V_{GS} = 5 \text{ V}; I_D = 50 \text{ A}; V_{DS} = 15 \text{ V};$ 8 T_i = 25 °C; see Figure 11

Suitable for logic level gate drive sources



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2. Pinning information

Table 2.	Pinning	information			
Pin	Symbol	Description	Simplified outline	Graphic symbol	
1	G	gate		_	
2	D	drain ^[1]	mb		
3	S	source			
mb	D mounting base; connected to dra	mounting base; connected to drain		mbbo76 S	
			SOT428 (DPAK)		

[1] It is not possible to make a connection to pin 2.

3. Ordering information

Table 3. Ordering information

Type number	Package			
	Name	Description	Version	
PHD101NQ03LT	DPAK	plastic single-ended surface-mounted package (DPAK); 3 leads (one lead cropped)	SOT428	

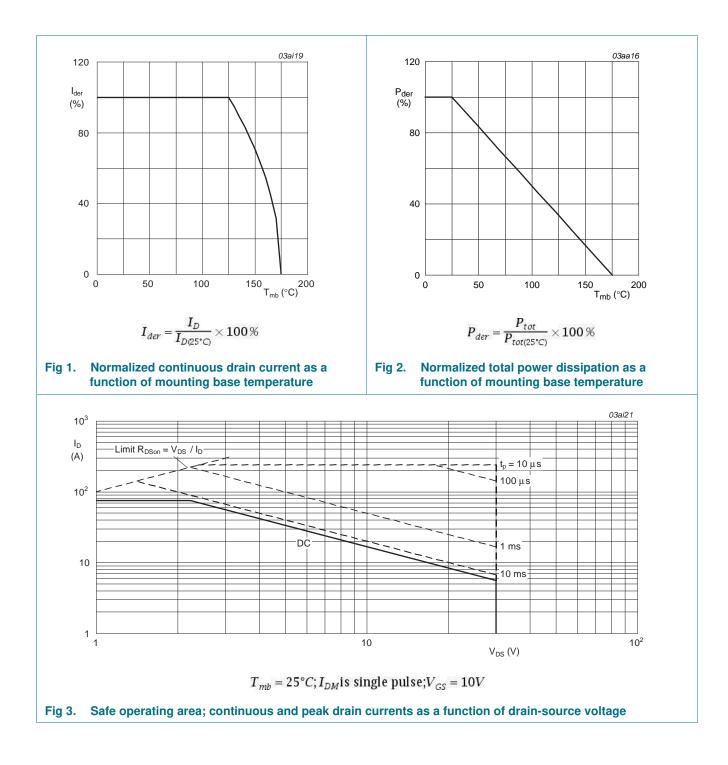
4. Limiting values

Table 4. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions	Min	Мах	Unit
V _{DS}	drain-source voltage	T _j ≥ 25 °C; T _j ≤ 175 °C	-	30	V
V _{DGR}	drain-gate voltage	$T_j \ge 25 \text{ °C}; T_j \le 175 \text{ °C}; R_{GS} = 20 \text{ k}\Omega$	-	30	V
V _{GS}	gate-source voltage		-20	20	V
I _D	drain current	V_{GS} = 10 V; T_{mb} = 100 °C; see <u>Figure 1</u>	-	75	А
		V_{GS} = 10 V; T_{mb} = 25 °C; see <u>Figure 1</u> ; see <u>Figure 3</u>	-	75	A
I _{DM}	peak drain current	pulsed; $t_p \le 10 \ \mu s$; $T_{mb} = 25 \ ^{\circ}C$; see Figure 3	-	240	А
P _{tot}	total power dissipation	T _{mb} = 25 °C; see <u>Figure 2</u>	-	166	W
T _{stg}	storage temperature		-55	175	°C
Tj	junction temperature		-55	175	°C
V _{GSM}	peak gate-source voltage	pulsed; $\delta = 25$ %; $t_p \le 50 \ \mu s$	-25	25	V
Source-drai	n diode				
I _S	source current	T _{mb} = 25 °C	-	75	А
I _{SM}	peak source current	pulsed; $t_p \le 10 \ \mu s$; $T_{mb} = 25 \ ^{\circ}C$	-	240	А
Avalanche r	ruggedness				
$E_{DS(AL)S}$	non-repetitive drain-source avalanche energy	$ \begin{array}{l} V_{GS} = 10 \; V; \; T_{j(init)} = 25 \; ^{\circ}C; \; I_{D} = 43 \; A; \\ V_{sup} \leq 15 \; V; \; unclamped; \; t_{p} = 0.19 \; ms; \\ R_{GS} = 50 \; \Omega \end{array} $	-	185	mJ
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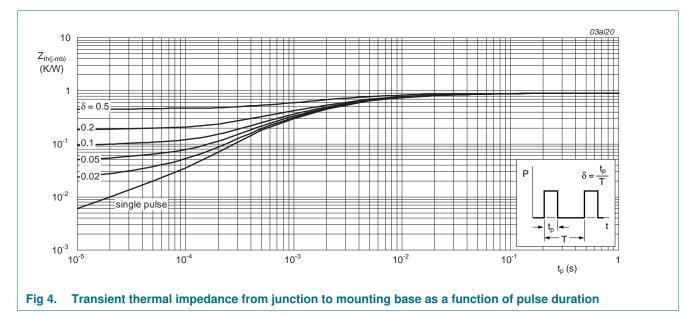


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5. Thermal characteristics

Table 5.	Thermal characteristics						
Symbol	Parameter	Conditions		Min	Тур	Max	Unit
$R_{th(j-mb)}$	thermal resistance from junction to mounting base	see <u>Figure 4</u>		-	-	0.9	K/W
R _{th(j-a)}	thermal resistance from junction to ambient	minimum footprint	[1]	-	75	-	K/W
		SOT404 minimum footprint	[1]	-	50	-	K/W

[1] Mounted on a printed-circuit board; vertical in still air.



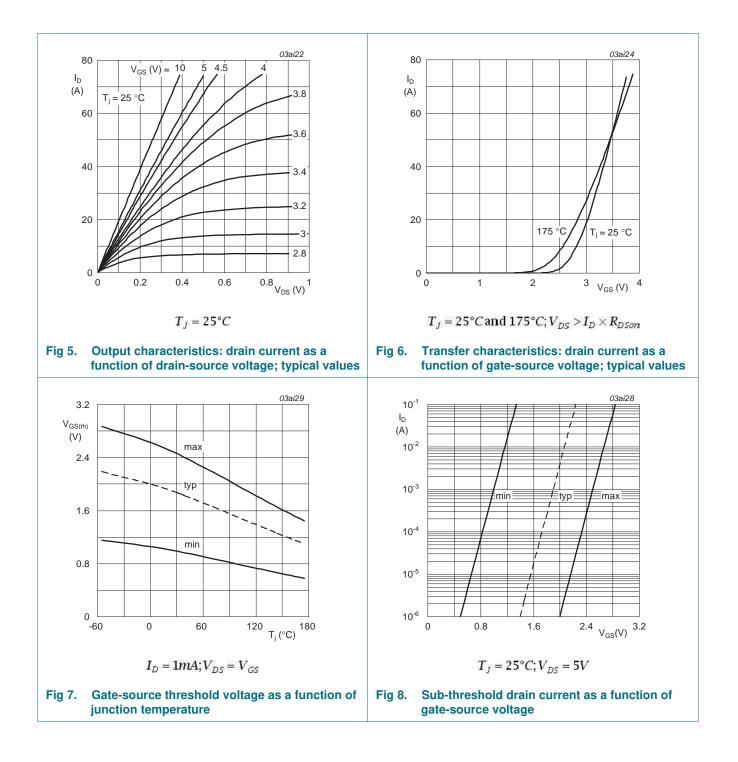
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6. Characteristics

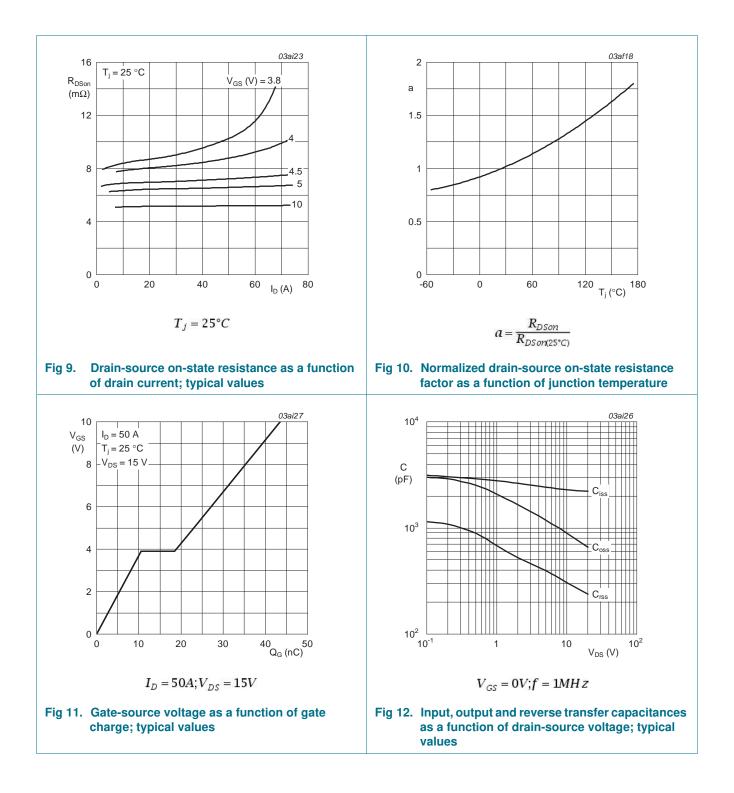
Table 6.	Characteristics					
Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Static cha	aracteristics					
V _{(BR)DSS}	drain-source breakdown voltage	$I_D = 250 \ \mu A; \ V_{GS} = 0 \ V; \ T_j = -55 \ ^\circ C$	27	-	-	V
		$I_D = 250 \ \mu\text{A}; \ V_{GS} = 0 \ V; \ T_j = 25 \ ^\circ\text{C}$	30	-	-	V
V _{GS(th)}	gate-source threshold voltage	I _D = 1 mA; V _{DS} = V _{GS} ; T _j = 175 °C; see <u>Figure 7</u> ; see <u>Figure 8</u>	0.6	-	-	V
		$I_D = 1 \text{ mA}; V_{DS} = V_{GS}; T_j = -55 \text{ °C};$ see <u>Figure 7</u> ; see <u>Figure 8</u>	-	-	2.9	V
		I _D = 1 mA; V _{DS} = V _{GS} ; T _j = 25 °C; see <u>Figure 7</u> ; see <u>Figure 8</u>	1	1.9	2.5	V
I _{DSS}	drain leakage current	$V_{DS} = 30 \text{ V}; V_{GS} = 0 \text{ V}; T_j = 25 \text{ °C}$	-	0.05	1	μA
		$V_{DS} = 30 \text{ V}; V_{GS} = 0 \text{ V}; T_j = 175 \text{ °C}$	-	-	500	μA
I _{GSS}	gate leakage current	$V_{GS} = 20 \text{ V}; V_{DS} = 0 \text{ V}; T_j = 25 \text{ °C}$	-	10	100	nA
		V_{GS} = -20 V; V_{DS} = 0 V; T_j = 25 °C	-	10	100	nA
R _{DSon}	drain-source on-state resistance	V_{GS} = 10 V; I_D = 25 A; T_j = 25 °C; see <u>Figure 9</u> ; see <u>Figure 10</u>	-	4.5	5.5	mΩ
		$V_{GS} = 5 \text{ V}; I_D = 25 \text{ A}; T_j = 175 \text{ °C};$ see <u>Figure 9</u> ; see <u>Figure 10</u>	-	10.5	13.5	mΩ
		V _{GS} = 5 V; I _D = 25 A; T _j = 25 °C; see <u>Figure 9</u> ; see <u>Figure 10</u>	-	5.8	7.5	mΩ
Dynamic	characteristics					
Q _{G(tot)}	total gate charge	$I_D = 50 \text{ A}; V_{DS} = 15 \text{ V}; V_{GS} = 5 \text{ V};$	-	23	-	nC
Q _{GS}	gate-source charge	$T_j = 25 \text{ °C}; \text{ see } \frac{\text{Figure } 11}{1}$	-	10.5	-	nC
Q _{GD}	gate-drain charge		-	8	-	nC
C _{iss}	input capacitance	$V_{DS} = 25 V; V_{GS} = 0 V; f = 1 MHz;$	-	2180	-	pF
C _{oss}	output capacitance	$T_j = 25 \text{ °C}; \text{ see } \frac{\text{Figure } 12}{12}$	-	600	-	pF
C _{rss}	reverse transfer capacitance		-	225	-	pF
t _{d(on)}	turn-on delay time	$V_{DS} = 15 \; V; \; R_L = 0.6 \; \Omega; \; V_{GS} = 4.5 \; V; \;$	-	23	-	ns
t _r	rise time	$R_{G(ext)} = 5.6 \ \Omega; \ T_j = 25 \ ^{\circ}C; \ I_D = 25 \ A$	-	90	-	ns
t _{d(off)}	turn-off delay time		-	37	-	ns
t _f	fall time		-	33	-	ns
Source-d	rain diode					
V _{SD}	source-drain voltage	I _S = 25 A; V _{GS} = 0 V; T _j = 25 °C; see <u>Figure 13</u>	-	0.85	1.2	V
t _{rr}	reverse recovery time	$I_{S} = 10 \text{ A}; \text{ d}I_{S}/\text{d}t = -100 \text{ A}/\mu\text{s};$	-	37	-	ns
Q _r	recovered charge	$V_{GS} = 0 \text{ V}; V_{DS} = 25 \text{ V}; T_j = 25 \text{ °C}$	-	33	-	nC

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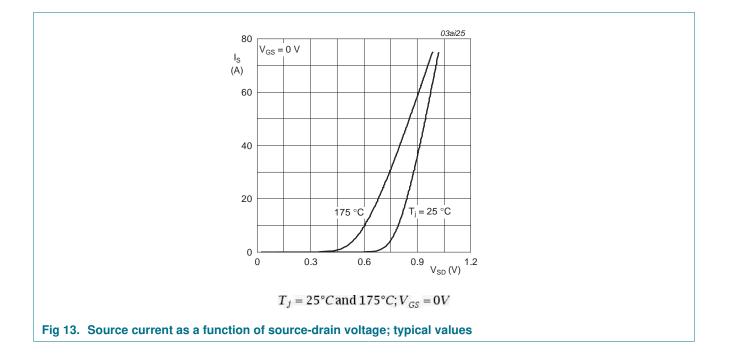
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7. Package outline

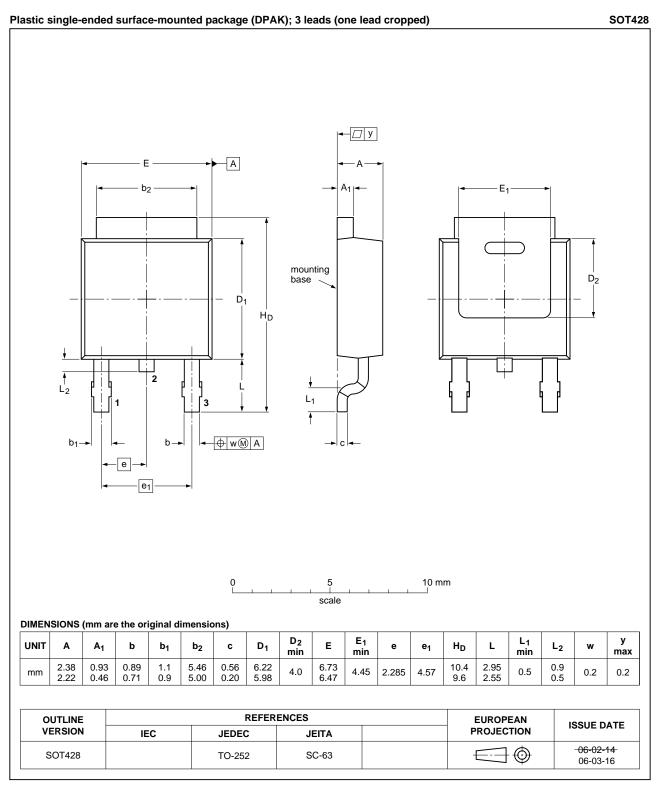


Fig 14. Package outline SOT428 (DPAK)

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8. Revision history

Table 7.Revision h	nistory			
Document ID	Release date	Data sheet status	Change notice	Supersedes
PHD101NQ03LT v.5	20111031	Product data sheet	-	PHD101NQ03LT v.4
Modifications:	 Various changes 	to content.		
PHD101NQ03LT v.4	20090609	Product data sheet	-	PHD101NQ03LT v.3

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9. Legal information

9.1 Data sheet status

Document status [1] [2]	Product status [3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
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Product [short] data sheet	Production	This document contains the product specification.

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